## Diana Nesheva

List of Publications by Year in descending order

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471509 454955 1,206 94 17 30 citations h-index g-index papers 97 97 97 999 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Raman scattering and photoluminescence from Si nanoparticles in annealed SiOx thin films. Journal of Applied Physics, 2002, 92, 4678-4683.	2.5	182
2	Size-Dependent Properties of Sonochemically Synthesized Three-Dimensional Arrays of Close-Packed Semiconducting AgBiS <sub>2</sub> Quantum Dots. Chemistry of Materials, 2008, 20, 2551-2565.	6.7	77
3	Preparation and characterization of amorphous SeTe/CdSe superlattices and their constituent thin layers. Thin Solid Films, 1992, 213, 230-234.	1.8	46
4	Composition, structure and annealing-induced phase separation in SiOx films produced by thermal evaporation of SiO in vacuum. Vacuum, 2002, 68, 1-9.	3.5	46
5	Photoconductivity and Relaxation Dynamics in Sonochemically Synthesized Assemblies of AgBiS <sub>2</sub> Quantum Dots. Journal of Physical Chemistry C, 2011, 115, 37-46.	3.1	46
6	Rheological, electrical, and microwave properties of polymers with nanosized carbon particles. Journal of Applied Polymer Science, 2004, 92, 2220-2227.	2.6	44
7	Raman Scattering from ZnSe Nanolayers. Acta Physica Polonica A, 2009, 116, 75-77.	0.5	39
8	Photoluminescence of CdSe nanocrystals embedded in a SiOx thin film matrix. Journal of Luminescence, 1999, 82, 233-240.	3.1	28
9	Resonant Raman scattering and photoluminescence inSiOx/CdSemultiple quantum wells. Physical Review B, 1998, 58, 7913-7920.	3.2	25
10	Nanocrystals of CdSe in thin film matrix. Semiconductor Science and Technology, 1997, 12, 1319-1322.	2.0	24
11	On the structural stability of amorphous Se/CdSe multilayers: a Raman study. Journal of Non-Crystalline Solids, 1998, 224, 283-290.	3.1	24
12	Experimental studies on the defect states at the interface between nanocrystalline CdSe and amorphous SiOx. Journal of Physics Condensed Matter, 2000, 12, 751-759.	1.8	24
13	Composition and temperature dependence of the low-frequency Raman scattering in Ge–As–S glasses. Journal of Non-Crystalline Solids, 2004, 347, 187-196.	3.1	22
14	Formation of CdSe nanoclusters in SiOx thin films. Solid State Communications, 2000, 114, 511-514.	1.9	21
15	Absorption and transport properties of Si rich oxide layers annealed at various temperatures. Semiconductor Science and Technology, 2008, 23, 045015.	2.0	21
16	Microstructural characterization of thin SiOx films obtained by physical vapor deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 174, 132-136.	3.5	21
17	Memory effect in MIS structures with amorphous silicon nanoparticles embedded in ultra thin matrix. Journal of Physics and Chemistry of Solids, 2007, 68, 725-728.	4.0	20
18	Thin and superthin photoconductive CdSe films deposited at room substrate temperature. Journal of Materials Science, 1993, 28, 2183-2186.	3.7	19

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19	Nanoparticle layers of CdSe buried in oxide and chalcogenide thin film matrices. Vacuum, 2002, 65, 109-113.	3.5	18
20	Surface modification and chemical sensitivity of sol gel deposited nanocrystalline ZnO films. Materials Chemistry and Physics, 2018, 209, 165-171.	4.0	18
21	Gas sensitive ZnO thin films with desired (002) or (100) orientation obtained by ultrasonic spray pyrolysis. Materials Chemistry and Physics, 2014, 148, 712-719.	4.0	17
22	Stability of amorphous Se/Se100â^'xTex multilayers: A Raman study. Journal of Applied Physics, 1999, 86, 4964-4970.	2.5	16
23	Band and subband absorption of Se/CdSe amorphous multilayers. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1994, 70, 205-213.	0.6	14
24	Room temperature photoluminescence from amorphous silicon nanoparticles in SiOx thin films. Journal of Luminescence, 2007, 126, 497-502.	3.1	14
25	B12SiO20 monocrystals doped with transition metals. Journal of Physics and Chemistry of Solids, 1995, 56, 241-250.	4.0	13
26	Crystal structure and spectral photosensitivity of thermally evaporated ZnxCd1â^'xSe thin films. Journal Physics D: Applied Physics, 2011, 44, 415305.	2.8	13
27	Influence of 20 MeV electron irradiation on the optical properties and phase composition of SiOx thin films. Journal of Applied Physics, 2018, 123, 195303.	2.5	12
28	Photoconductivity and recombination in amorphous Se/CdSe multilayers. Thin Solid Films, 1996, 280, 51-55.	1.8	11
29	Exciton related resonant Raman scattering from CdSe quantum dots in an amorphous GeS2thin film matrix. Journal of Physics Condensed Matter, 2004, 16, 8221-8232.	1.8	11
30	Composition and structure of Zn $<$ sub $>$ x $<$ /sub $>$ Cd $<$ sub $>$ 1 $\hat{a}$ °x $<$ /sub $>$ Se single layers prepared by thermal evaporation of ZnSe and CdSe. Journal of Physics: Conference Series, 2010, 253, 012035.	0.4	11
31	Photoconductivity of amorphous CdS films. Journal of Non-Crystalline Solids, 1982, 51, 381-388.	3.1	10
32	Characterization of amorphous selenium sublayers in chalcogenide superlattices by Raman scattering. Solid State Communications, 1992, 82, 959-962.	1.9	10
33	Small-angle X-ray diffraction studies on interface sharpness of amorphous Se/CdSe superlattices. Journal of Non-Crystalline Solids, 1995, 191, 205-208.	3.1	10
34	Metal-Oxide-Semiconductor Structures Containing Silicon Nanocrystals for Application in Radiation Dosimeters. Sensor Letters, 2012, 10, 833-837.	0.4	10
35	Stepwise optical absorption in amorphous SeTe/CdSe superlattices. Superlattices and Microstructures, 1992, 11, 439-443.	3.1	9
36	Traps and recombination centers in pure and Co-doped Bi12SiO20 crystals. Journal of Physics and Chemistry of Solids, 1993, 54, 857-862.	4.0	9

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37	Some properties of Bi12SiO20:Fe doped crystals. Journal of Physics and Chemistry of Solids, 1994, 55, 889-894.	4.0	9
38	LiNbO/sub 3/ optical waveguides formed in a new proton source. Journal of Lightwave Technology, 2002, 20, 71-77.	4.6	9
39	Photoreflectance study of multilayer structures of nanocrystalline CdSe in insulator matrix. Thin Solid Films, 2006, 495, 338-342.	1.8	9
40	Compositional Dependences of Some Optical and Electrical Properties of the GexAs40—xSe60 System. Physica Status Solidi A, 1999, 172, 149-154.	1.7	8
41	MOS structures containing silicon nanoparticles for memory device applications. Journal of Physics: Conference Series, 2008, 113, 012034.	0.4	8
42	Photoluminescence from SiO <sub><i>x</i></sub> layers containing amorphous silicon nanoparticles. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 746-751.	1.8	8
43	Characterization of Si–SiOx nanocomposite layers by comparative analysis of computer simulated and experimental infra-red transmission spectra. Thin Solid Films, 2012, 520, 2085-2091.	1.8	8
44	Application of Metal-Oxide-Semiconductor structures containing silicon nanocrystals in radiation dosimetry. Open Physics, 2015, 13, .	1.7	8
45	Properties of laser-beam sputtered CdS thin films. Journal of Materials Science Letters, 1985, 4, 442-444.	0.5	7
46	Electrophotographic photoreceptors including selenium-based multilayers. Semiconductor Science and Technology, 1997, 12, 595-599.	2.0	7
47	Formation of Si Nanocrystals in Thin SiO <sub>2</sub> Films for Memory Device Applications. Materials Science Forum, 2010, 644, 101-104.	0.3	7
48	Structural, compositional and electrical characterization of Si-rich SiOx layers suitable for application in light sensors. Materials Science in Semiconductor Processing, 2015, 37, 229-234.	4.0	7
49	UV Sensitivity of MOS Structures with Silicon Nanoclusters. Sensors, 2019, 19, 2277.	3.8	7
50	Studies of low-energy optical absorption and gap state density of a-CdS by the constant photocurrent method. Physica Status Solidi A, 1984, 82, 243-248.	1.7	6
51	Thin film semiconductor nanomaterials and nanostructures prepared by physical vapour deposition: An atomic force microscopy study. Journal of Physics and Chemistry of Solids, 2007, 68, 675-680.	4.0	6
52	Effect of oxygen to argon ratio on the properties of thin SiO x films deposited by r.f. sputtering. Journal of Materials Science: Materials in Electronics, 2010, 21, 481-485.	2.2	6
53	"Cymatics―of selenium and tellurium films deposited in vacuum on vibrating substrates. Surface and Coatings Technology, 2016, 307, 542-546.	4.8	6
54	Changes in the photosensitivity and dark conductivity of CdS single crystals after illumination at high temperature. Journal of Physics and Chemistry of Solids, 1984, 45, 201-206.	4.0	5

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55	Properties of amorphous CdS-crystalline Si junctions. Solid-State Electronics, 1987, 30, 173-176.	1.4	5
56	Influence of crystallization on electrical and optical properties of Teî—'Seî—'Sn and Teî—'Seî—'Snî—'O films. Journal of Non-Crystalline Solids, 1993, 160, 105-110.	3.1	5
57	Title is missing!. Journal of Materials Science: Materials in Electronics, 2003, 14, 799-800.	2.2	5
58	Infrared and Photoluminescence Study of Rapidly Thermally Annealed SiO <sub>x</sub> Thin Films. Materials Science Forum, 2007, 555, 309-314.	0.3	5
59	Radiation Dosimeter Based on Metal-Oxide-Semiconductor Structures Containing Silicon Nanocrystals. Key Engineering Materials, 0, 495, 120-123.	0.4	5
60	Phase characterization and ethanol adsorption in TiO2 nanotubes anodically grown on Ti6Al4V alloy substrates. Journal of Alloys and Compounds, 2019, 798, 394-402.	5.5	5
61	Modification of surface morphology and lattice order in nanocrystalline ZnO thin films prepared by spin-coating sol–gel method. Journal of Sol-Gel Science and Technology, 2021, 100, 55-67.	2.4	5
62	NANOCRYSTALLINE AND AMORPHOUS THIN FILM SYSTEMS INCLUDING LOW-DIMENSIONAL CHALCOGENIDE MATERIALS. , 2001, , 239-279.		5
63	Characterization of ZnSe Nanolayers by Spectroscopic Ellipsometry. Acta Physica Polonica A, 2009, 116, 708-711.	0.5	5
64	Computational analysis of thermally stimulated currents in Bi12TiO20 single crystals. Journal of Applied Physics, 2006, 100, 053704.	2.5	4
65	TEM and Spectroscopic Ellipsometry studies of multilayer gate dielectrics containing crystalline and amorphous Si nanoclusters. Physica E: Low-Dimensional Systems and Nanostructures, 2013, 51, 111-114.	2.7	4
66	Effect of the composition and annealing on the electron transport in ZnxCd1â^'xSe nanocrystalline films. Journal of Alloys and Compounds, 2014, 586, 650-655.	5.5	4
67	Interface and structural disorder changes in Se/CdSe multilayers. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1995, 72, 67-73.	0.6	3
68	Thermal stability of amorphous multilayers. Solid State Communications, 1997, 103, 431-434.	1.9	3
69	Charge transport in CdSe nanocrystalline sublayers of SiOx/CdSe multilayers and composite SiOx-CdSe thin films. Journal of Physics Condensed Matter, 2000, 12, 3967-3974.	1.8	3
70	Study of modified solid surfaces by nanostructured CdSe in SiOxthin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1070-1074.	0.8	3
71	Selective photosensitivity of metal–oxide–semiconductor structures with SiOx layer annealed at high temperature. Journal of Materials Science: Materials in Electronics, 2020, 31, 17412-17421.	2.2	3
72	Influence of annealing on photoinduced phenomena in CdS. Journal Physics D: Applied Physics, 1985, 18, 677-683.	2.8	2

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73	Photovoltaic and Electroluminescent Properties of Stainetched Porous Silicon Based Heterojunctions. Materials Research Society Symposia Proceedings, 1995, 405, 167.	0.1	2
74	Thickness Dependent Photocrystallization in Se/Se70Te30 Amorphous Multilayers. Physica Status Solidi A, 1999, 176, R3-R4.	1.7	2
75	Defect states in CdSe nanocrystalline layers. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 1081-1087.	1.8	2
76	Dependence of photoluminescence from a-Si nanoparticles on the annealing time and exciting wavelength. Journal of Luminescence, 2007, 126, 7-13.	3.1	2
77	Modulated photoconductivity study of nanocrystalline CdSe films. Journal of Non-Crystalline Solids, 2008, 354, 2744-2747.	3.1	2
78	Temperature Dependence of the Photoluminescence from Ensembles of Amorphous Silicon Nanoparticles with Various Average Sizes. Journal of Nanoscience and Nanotechnology, 2011, 11, 959-965.	0.9	2
79	Raman scattering characterization of ZnSe/Zn <sub>0.6</sub> Cd <sub>0.4</sub> Se multilayers prepared by thermal vacuum evaporation. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 949-952.	1.8	2
80	Changes in composite nc-Si-SiO2 thin films caused by 20â€MeV electron irradiation. Nuclear Instruments & Methods in Physics Research B, 2019, 458, 159-163.	1.4	2
81	Room temperature sensitivity of ZnSe nanolayers to ethanol vapours. Journal of Physics: Conference Series, 2019, 1186, 012023.	0.4	2
82	Influence of fast neutron irradiation on the phase composition and optical properties of homogeneous SiOx and composite Si–SiOx thin films. Journal of Materials Science, 2021, 56, 3197-3209.	3.7	2
83	Optical spectra of doped Bi12TiO20crystals. Journal of Physics Condensed Matter, 1994, 6, 11167-11175.	1.8	1
84	MOS Structures Containing Si Nanocrystals for Applications in UV Dosimeters. Key Engineering Materials, 0, 605, 380-383.	0.4	1
85	Effect of infrared laser irradiation on electrical conductivity and ethanol sensitivity of sol-gel ZnO thin films. Journal of Physics: Conference Series, 2021, 1762, 012037.	0.4	1
86	SPM electrical characterization of Ti/Al $\hat{a} \in$ Based ohmic contacts for sub-micron devices. , 2010, , .		0
87	Electrical Characterization of MOS Structures with Silicon Nanocrystals Suitable for X-Ray Detection. Key Engineering Materials, 0, 543, 150-153.	0.4	0
88	Effects of the preparation conditions and furnace annealing on the structure and morphology of Zn <inf>0.8</inf> Cd <inf>0.2</inf> Se thin films. , 2013, , .		0
89	Long term ageing changes in structure and morphology of nanocrystalline ZnxCd1 $\hat{a}$ °xSe thin films. , 2015, , .		0
90	Raman Study of Compositional Variations in ZnxCd1â^'xSe Films Prepared by Thermal Vacuum Evaporation. Journal of Nanoscience and Nanotechnology, 2016, 16, 8513-8518.	0.9	0

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91	Resistive switching behavior of SiOxlayers with Si nanoparticles. Journal of Physics: Conference Series, 2017, 794, 012018.	0.4	0
92	Properties of ZnSe nanocrystalline thin films prepared by thermal evaporation. Journal of Physics: Conference Series, 2021, 1762, 012036.	0.4	0
93	Raman Scattering from Low-Dimensional Semiconductors. , 2005, , 317-322.		0
94	Size-Dependent Absorption and Defect States in CdSe Nanocrystals in Various Multilayer Structures. Journal of Nanoscience and Nanotechnology, 2002, 2, 645-652.	0.9	0